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	Application No.	Applicant(s)	
Notice of Allowability	10/821,944	HAYASHIDA ET AL.	
	Examiner	Art Unit	
	David Nhu	2818	-
The MAILING DATE of this communication appe All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in to or other appropriate commur GHTS. This application is su	his application. If not includ ication will be mailed in due	ed course. THIS
1. This communication is responsive to <u>9/9/05</u> .			
2. The allowed claim(s) is/are <u>1-32</u> .			
 3.	been received. been received in Application cuments have been received of this communication to file at ENT of this application. Itted. Note the attached EXAM is reason(s) why the oath or country to be submitted. It be submitted. It be submitted. It has a point of the attached of the submitted. It has a point of the attached EXAM is reason(s) why the oath or country the submitted. It has a point of the submitted of the submitted. It has a point of the submitted of the submitte	No. 09/473,708. In this national stage application this national stage application reply complying with the red MINER'S AMENDMENT or National stage application is deficient. (PTO-948) attached the Office action of the Office action of the drawings in the front (not the	quirements
6. DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT for the comment of the	sit of BIOLOGICAL MATER	RIAL must be submitted. I	Note the
Attachment(s) 1. ☐ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☐ Information Disclosure Statements (PTO-1449 or PTO/SB/0-Paper No./Mail Date 4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material	6. ☐ Interview Sur Paper No./M 8), 7. ☐ Examiner's A 8. ☑ Examiner's S 9. ☐ Other	rmal Patent Application (PTonmary (PTO-413), lail Date mendment/Comment tatement of Reasons for Allo	ŕ

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REASONS FOR ALLOWANCE

- Claims 1-32 are allowed.
- 2. The following is an examiner's statement of reasons for allowance: None of the references of record teaches or suggests as cited in claims 1, 3, 5, 7, 8, 10, 13, 16, 17, 18, 19, 21, 24, 26, 29; an n-type GaN-based compound is formed on a substrate using ammonia as a raw material, characterized in that the ammonia is charged into a charging container so that at least a portion of the ammonia is in a liquid phase and in that the liquid phase ammonia has a water concentration of 0.01 to 0.5 vol. ppm. (as cited in claims 1, 3, 5, 8, 10, 13, 21, 24, 26); an n-type GaN-based compound is formed on a substrate using ammonia as a raw material, characterized in that the ammonia is charged in a gaseous state into reaction chamber housing therein the substrate so that at least a portion of the ammonia is in a liquid phase and in that the liquid phase ammonia has a water concentration of 0.01 to 0.5 vol. ppm as determined by FT-IR (as cited in claims 7, 16, 29); a GaN-based compound semiconductor, characterized by comprising a charging container and ammonia charged into the charging container so that at least a portion of the ammonia is in a liquid phase and characterized in t hat the liquid phase ammonia has a water concentration of 0.01 to 0.5 vol. ppm and in that the charging container is made of manganese steel or aluminum alloy; an inner surface subjected to plating treatment and polishing treatment; a cylindrical shape (as cited in claims 17, 18, 19). Applicants' undersigned representatives filed an amendment on 9/9/05, and also filed at that time a terminal disclaimer statement with reference to USP: 6,719,842 B2.
- 3. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the

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issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons

for Allowance."

Conclusion

4. The prior art made of record and not relied upon is considered pertinent to applicant's

disclosure: Hayashida et al (6,719,842 B2): Ammonia for Use in Manufacturing of GAN-Type

Compound Semiconductor and Method for Manufacturing GA-Type Compound

Semiconductor.

5. Any inquiry concerning this communication on earlier communications from the examiner

should be directed to David Nhu, (571)272-1792. The examiner can normally be reached

on Monday-Friday from 7:30 AM to 5:00 PM.

The examiner's supervisor, David Nelms can be reached on (571)272-1787.

The fax phone number for the organization where this application or proceeding is assigned is

(703)872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should

be directed to the receptionist whose telephone number is (703) 308-0956

David Nhu

September 21, 2005

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Replacement Sheet
U.S. Application No.: 10/821,944
Inventor: Hideki HAYASHIDA et al.
Group Art Unit: 2818 / Conf. No. 2372
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